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			Issue Date			Not applicable			
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_	nformation Disclosure Statement		Small Entity S	tatement					
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	Boston, M	IA 02109		Date: August 16, 200 Reg. No. 44,381	υD	Natasha C. Us			
		(617) 570- (617) 523-1		Tel. No.: (617) 570-					
		No. 05141		Fax No.: (617) 523-	-12.	Goodwin Procter LLP Exchange Place Boston, MA 02109			

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PATENT Attorney Docket No. MIT-160

# IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

APPLICANT(S):

Ariel et al.

SERIAL NO.:

10/823,083

**GROUP NO.:** 

1745

FILING DATE:

April 13, 2004

**EXAMINER:** 

Not yet assigned

TITLE:

INTEGRATED THIN FILM BATTERIES ON SILICON

**INTEGRATED CIRCUITS** 

## CERTIFICATE OF FIRST CLASS MAILING UNDER 37 C.F.R. 1.8

I hereby certify that this correspondence, and any document(s) referred to as enclosed herein, is/are being deposited with the United States Postal Service as first class mail, postage prepaid, in an envelope addressed to the Mail Stop Amendment, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450 on this 16<sup>th</sup> day of August, 2005.

Wendy L. Martin

Mail Stop Amendment Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

#### Submitted herewith are:

- 1. Transmittal Form (1 page);
- 2. Information Disclosure Statement (2 pages);
- 3. Form PTO-1449 (6 pages);
- 4. Copies of cited references B1-B3 and C1-C67; and
- 5. Return receipt postcard



### IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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Mail Stop Amendment Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

### INFORMATION DISCLOSURE STATEMENT

Sir:

In accordance with the provisions of 37 C.F.R. 1.97 and 1.98, Applicants hereby make of record the patents and publications listed on the accompanying Form PTO-1449, and other information contained herein, for consideration by the Examiner in connection with the examination of the above-identified patent application. In accordance with 37 C.F.R. 1.98(a)(2), only copies of the foreign patent documents and non-patent publications are enclosed.

#### REMARKS

In accordance with the provisions of 37 C.F.R. 1.97, this statement is being filed (CHECK ONE):

(1)	within three (3) months of the filing date of a national application other than a continued prosecution application under 37 C.F.R. 1.53(d), or within three (3) months of the date of entry of the national stage as set forth in 37 C.F.R. 1.491 in an international application, or before the mailing of the first Office action on the merits, or before the mailing of a first Office action after the filing of a request for continued examination under 37 C.F.R. 1.114; or
(2)	after the period defined in (1) but before the mailing date of a <b>final action</b> or a <b>notice</b> of allowance under 37 C.F.R. 1.311, and
	the requisite Statement is below, <b>OR</b>
	the requisite fee under 37 C.F.R. 1.17(p), namely \$180.00, is included herein, or

Information Disclosure Statement Serial No. 10/823,083 Page 2 of 2

	(3)	after the mailing date of a final action or notice of allo of the issue fee, AND	fter the mailing date of a final action or notice of allowance but before the paymen of the issue fee, AND							
		the requisite Statement is below, AND	he requisite Statement is below, AND							
		the requisite petition fee under 37 C.F.R. 1.17(p), namely \$180.00 is included he								
It is respectfully requested that each of the patents and publications listed on the attached Form PTO-1449, and other information contained herein, be made of record in this application.										
		Respectfully submitted,								
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	A2	6,242,132	06/05/2001	Neudecl	er et al.					
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	B2	97/19481	05/29/1997	wo				N		Y
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